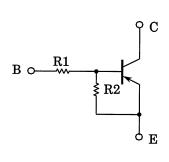
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2321A,RN2322A,RN2323A,RN2324A RN2325A,RN2326A,RN2327A

Switching, Inverter Circuit, Interface Circuit And Driver Circuit Applications

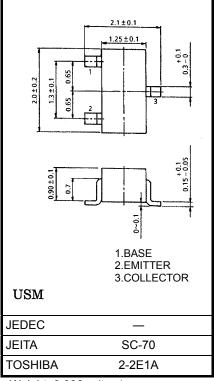
- High current driving is possible.
- Since bias resisters are built in the transistor, the miniaturization of the apparatus by curtailment of the number of parts and laborsaving of an assembly are possible.
- Many kinds of resistance value are lined up in order to support various kinds of circuit design.
- Complementary to RN1321A~RN1327A
- Low V_{CE(sat)} enable to be low power dissipation on high current driving.

Equivalent Circuit And Bias Resistance Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2321A	1	1
RN2322A	2.2	2.2
RN2323A	4.7	4.7
RN2324A	10	10
RN2325A	0.47	10
RN2326A	1	10
RN2327A	2.2	10

Unit in mm



Weight: 0.006 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteris	Symbol	Rating	Unit		
Collector-base voltage	RN2321A~2327A	V_{CBO}	-15	V	
Collector-emitter voltage	KINZJZ IA ZJZIA	V _{CEO}	-12	V	
	RN2321A~2324A		-10	٧	
Emitter-base voltage	RN2325A, 2326A	V _{EBO}	-5		
	RN2327A		-6		
Collector current		IC	-500	mA	
Collector power dissipation	RN2321A~2327A	PC	100	mW	
Junction temperature	KINZ3Z A~Z3Z A	Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

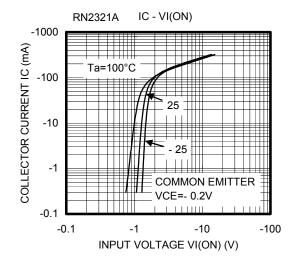
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

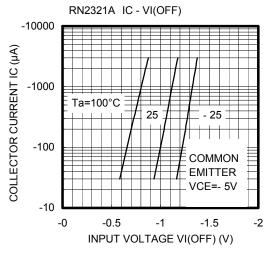
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

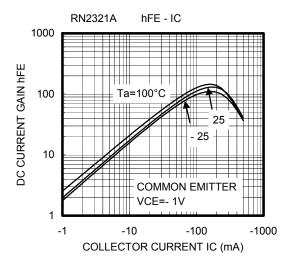


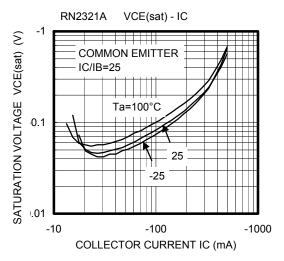
Electrical Characteristics (Ta = 25°C)

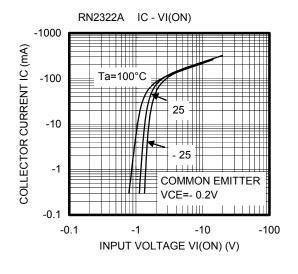
Characte	eristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN2321A~2327A	I _{CBO}		$V_{CB} = -15V$, $I_E = 0$	_	-	-100	nΔ
	INNESETA ESETA	I _{CEO}		$V_{CE} = -12V, I_B = 0$	_	-	-500	nA
	RN2321A	I _{EBO}		V _{EB} =–10V, I _C = 0	-3.85	_	-7.14	
	RN2322A		_		-1.75	_	-3.25	
	RN2323A				-0.82	_	-1.52	
Emitter cut-off current	RN2324A				-0.38	_	-0.71	mA
	RN2325A			V _{EB} = -5V, I _C = 0	-0.365	_	-0.682	
	RN2326A				-0.35	_	-0.65	
	RN2327A			$V_{EB} = -6V, I_C = 0$	-0.378		-0.703	
	RN2321A				35	_	_	
	RN2322A				65	_	_	
	RN2323A				100	_	_	
DC current gain	RN2324A	h _{FE}	_	V _{CE} = -1V, I _C =-50mA	140	_	_	
-	RN2325A	. –			140	_	_	
	RN2326A				140	_	_	
	RN2327A				140		_	
Collector-emitter	RN2321A			I _C = -50mA, I _B =-2mA				
saturation voltage	RN2322A~2327A	V _{CE} (sat)	_	I _C = -50mA, I _B =-1mA	<u> </u>	_	-0.25	V
Input voltage (ON)	RN2321A	VI (ON)		V _{CE} =-0.2V, I _C =-50mA	-1.0	_	-2.4	V
	RN2322A		_		-1.1	_	-2.7	
	RN2323A				-1.3	_	-3.5	
	RN2324A				-1.5	_	-5.2	
	RN2325A				-0.5	_	-1.2	
	RN2326A				-0.6	_	-1.4	
	RN2327A				-0.7	_	-1.9	
	RN2321A~2324A	VI (OFF)	_	$V_{CE} = -5V$, $I_{C} = -0.1$ mA	-0.8	_	-1.4	V
Input voltage (OFF)	RN2325A, 2326A				-0.4	_	-0.8	
	RN2327A				-0.5	_	-1.0	
Transition frequency	RN2321A~2327A	f _T	_	V _{CE} =-5V, I _C =-20mA	_	200	_	MHz
Collector Output capacitance	RN2321A~2327A	C _{ob}	_	V _{CB} = 10V, I _E = 0, f = 1MH _z	_	5	_	pF
Input resistor	RN2321A	R1	_	_	0.7	1	1.3	
	RN2322A				1.54	2.2	2.86	
	RN2323A				3.29	4.7	6.11	
	RN2324A				7	10	13	kΩ
	RN2325A				0.329	0.47	0.611	
	RN2326A				0.7	1	1.3	
	RN2327A				1.54	2.2	2.86	
Resistor ratio	RN2321A~2324A			_	0.85	1.0	1.15	
	RN2325A				0.040	0.047	0.054	
	RN2326A	R1/R2	₹1/R2 —		0.085	0.1	0.115	
	RN2327A				0.187	0.220	0.253	

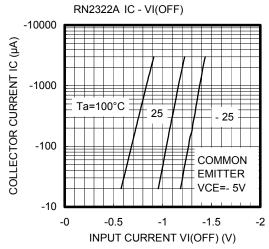


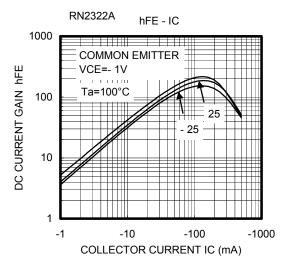


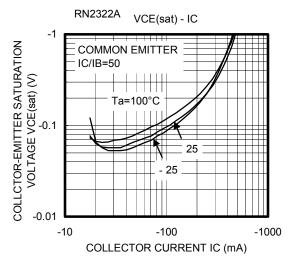


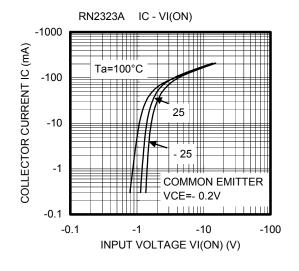


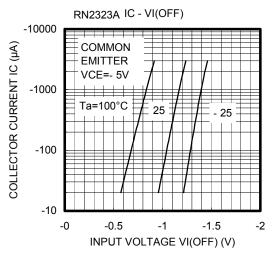


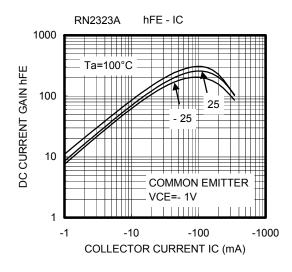


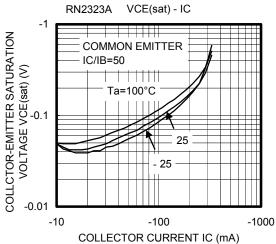




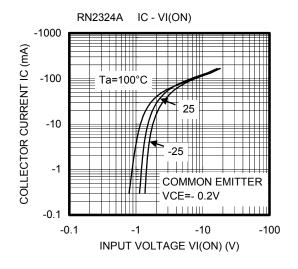


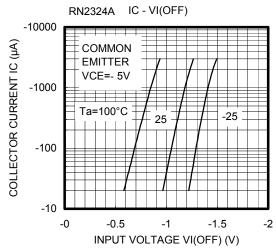


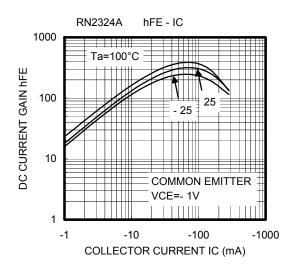


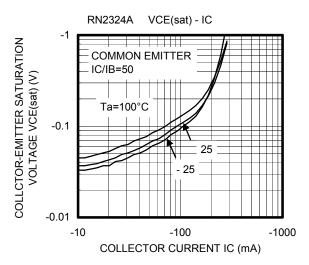


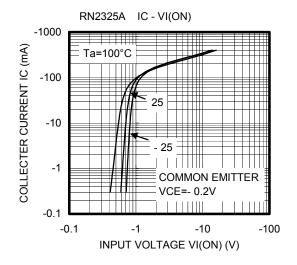
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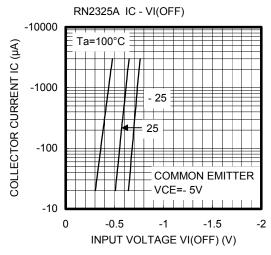


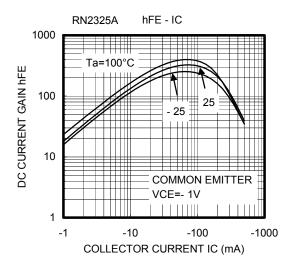


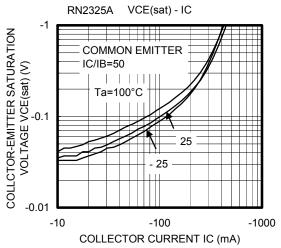


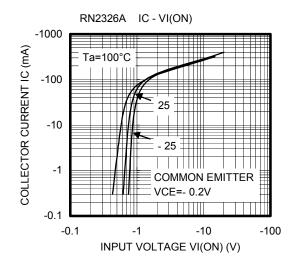


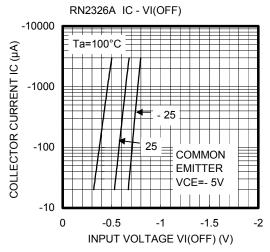


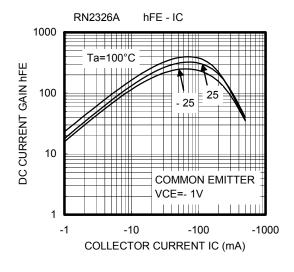


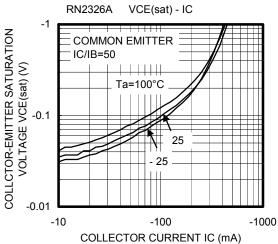


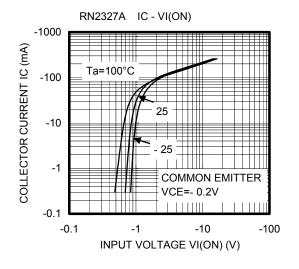


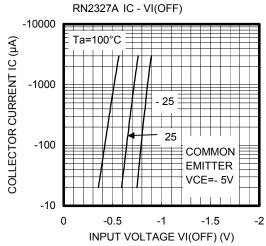


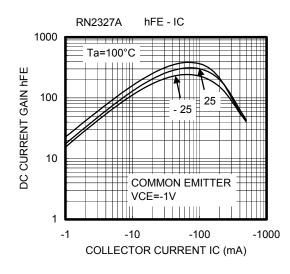


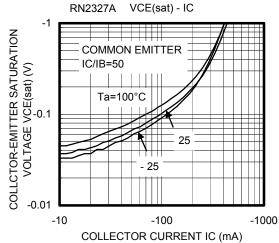












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Type Name	Marking
RN2321A	Type Name
RN2322A	Type Name RB
RN2323A	Type Name
RN2324A	Type Name R D
RN2325A	Type Name
RN2326A	Type Name
RN2327A	Type Name R G

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20070701-EN GENERAL

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